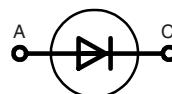


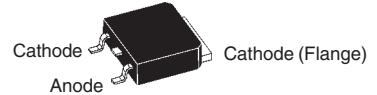
HiPerFRED™ Epitaxial Diode with soft recovery

$I_{FAVM} = 6 \text{ A}$
 $V_{RRM} = 600 \text{ V}$
 $t_{rr} = 20 \text{ ns}$

| V_{RSM} V | V_{RRM} V | Type | Marking on product |
|----------------|----------------|-------------|-----------------------|
| 600 | 600 | DSEP 6-06AS | 6P060AS |



TO-252AA (DPAK)



| Symbol | Conditions | Maximum Ratings | | | Features |
|--------------|--|-----------------|------------------|--|----------------------------------|
| I_{FRMS} | $T_{VJ} = T_{VJM}$ | 26 | A | | • Planar passivated chips |
| I_{FAVM} ① | $T_c = 152^\circ\text{C}$; rectangular, $d = 0.5$ | 6 | A | | • Very short recovery time |
| I_{FRM} | $t_p < 10 \mu\text{s}$; rep. rating, pulse width limited by T_{VJM} | 12 | A | | • Extremely low switching losses |
| I_{FSM} | $T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ | (50 Hz), sine | 40 | | • Low I_{RM} -values |
| A | | | | | • Soft recovery behaviour |
| E_{AS} | $T_{VJ} = 25^\circ\text{C}$; non-repetitive $I_{AS} = 0.8 \text{ A}$; $L = 180 \mu\text{H}$ | 0.1 | mJ | | |
| I_{AR} | $V_A = 1.5 \cdot V_R$ typ.; $f = 10 \text{ kHz}$; repetitive | 0.1 | A | | |
| T_{VJ} | | -40...+175 | $^\circ\text{C}$ | | |
| T_{VJM} | | 175 | $^\circ\text{C}$ | | |
| T_{stg} | | -40...+150 | $^\circ\text{C}$ | | |
| P_{tot} | $T_c = 25^\circ\text{C}$ | 55 | W | | |
| Weight | typ. | 0.3 | g | | |

| Symbol | Conditions | Characteristic Values | | |
|------------|---|-----------------------|---------------|----|
| | | typ. | max. | |
| I_R | $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 150^\circ\text{C}$ $V_R = V_{RRM}$ | 50 | μA | |
| | | 0.2 | mA | |
| V_F | $I_F = 6 \text{ A}$; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$ | 1.33 | V | |
| | | 2.02 | V | |
| R_{thJC} | | 2.8 | K/W | |
| t_{rr} | $I_F = 1 \text{ A}$; $-\text{di}/\text{dt} = 200 \text{ A}/\mu\text{s}$; $V_R = 30 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ | 20 | tbd | ns |
| I_{RM} | $V_R = 100 \text{ V}$; $I_F = 10 \text{ A}$; $-\text{di}_F/\text{dt} = 100 \text{ A}/\mu\text{s}$ $T_{VJ} = 100^\circ\text{C}$ | 3.5 | 4.4 | A |

① I_{FAVM} rating includes reverse blocking losses
at T_{VJM} , $V_R = 0.6 V_{RRM}$, duty cycle $d = 0.5$

Data according to IEC 60747

Applications

- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

Dimensions see pages D4 - 85-86

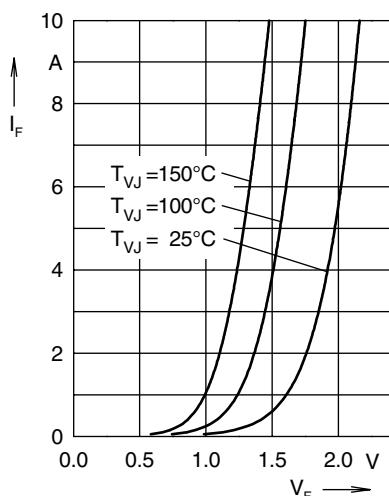


Fig. 1 Forward current I_F versus V_F

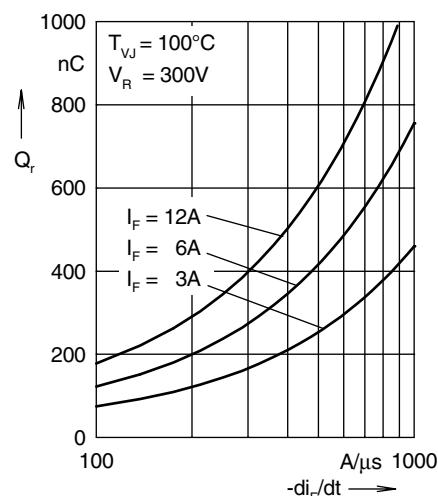


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

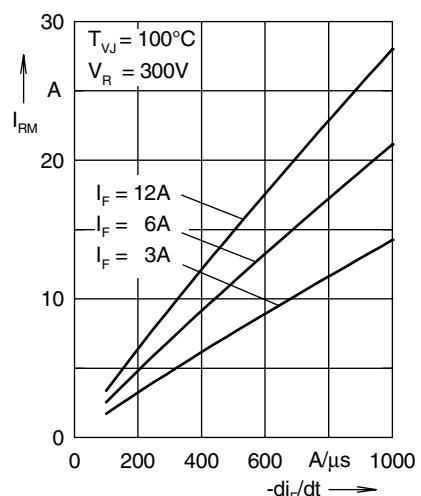


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

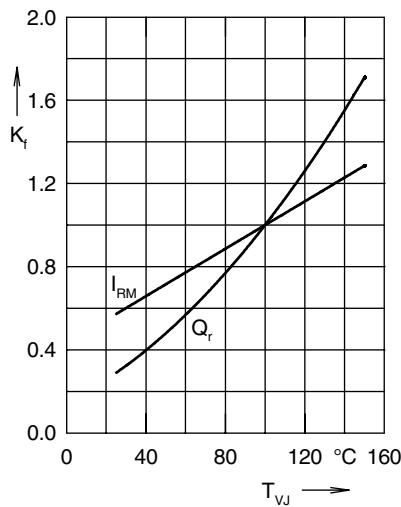


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

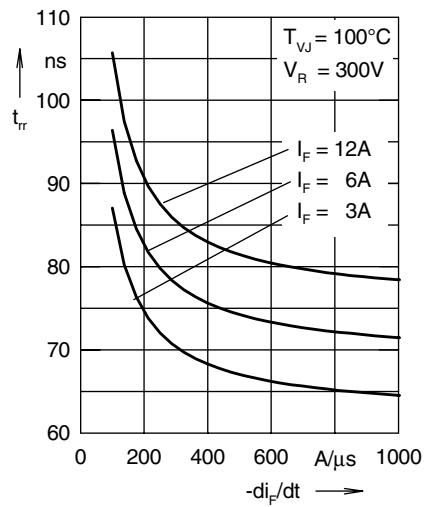


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

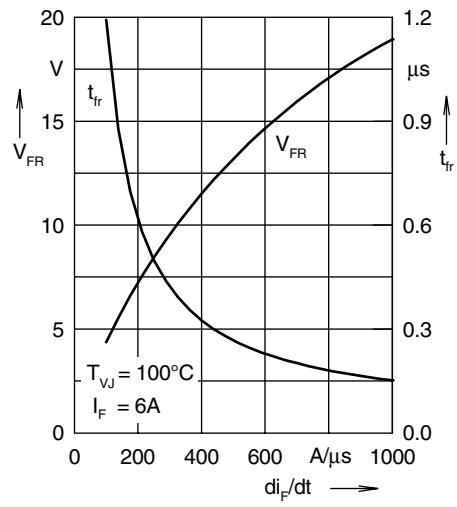


Fig. 6 Peak forward voltage $V_{FR} + t_{fr}$ versus di_F/dt

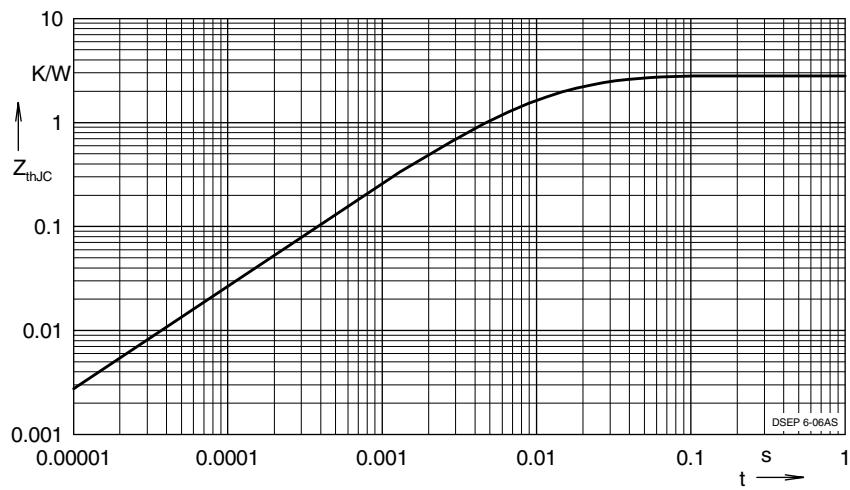


Fig. 7 Transient thermal resistance junction to case

NOTE: Fig. 2 to Fig. 6 shows typical values